

**8M-BIT MASK-PROGRAMMABLE ROM
1M-WORD BY 8-BIT (BYTE MODE)/512K-WORD BY 16-BIT (WORD MODE)****Description**

The μ PD23C8000X is a 8, 388, 608 bits mask-programmable ROM. The word organization is selectable (BYTE mode: 1, 048, 576 words by 8 bits, WORD mode: 524, 288 words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.

The μ PD23C8000X is packed in 42-pin plastic DIP, 44-pin plastic SOP, 48-pin plastic TSOP (I), and 44-pin plastic TSOP (II).

Features

- Word organization:
 - 1, 048, 576 words by 8 bits (BYTE mode)
 - 524, 288 words by 16 bits (WORD mode)
- Access time: 120 ns (MAX.):
- Low current consumption
 - Active 50 mA (MAX.)
 - Standby 100 μ A (MAX.) (CMOS level input)

**Ordering Information**

Part Number	Package
μ PD23C8000XCZ-XXX	42-pin Plastic DIP (600 mil)
μ PD23C8000XGX-XXX	44-pin Plastic SOP (600 mil)
μ PD23C8000XGY-XXX-MJH	48-pin Plastic TSOP (I) (12 × 18 mm) (Normal bent)
μ PD23C8000XGY-XXX-MKH	48-pin Plastic TSOP (I) (12 × 18 mm) (Reverse bent)
μ PD23C8000XG5-XXX-7JF	44-pin Plastic TSOP (II) (400 mil) (Normal bent)

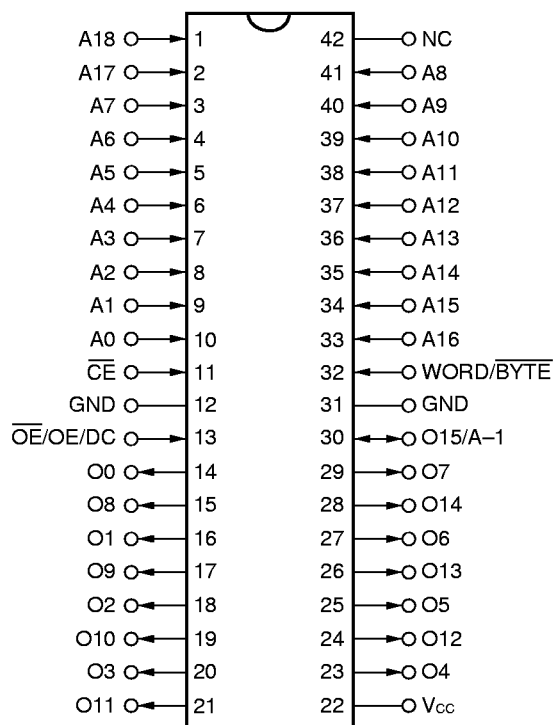
(XXX: ROM code suffix No.)

The information in this document is subject to change without notice.

★ Pin Configuration (Marking Side)

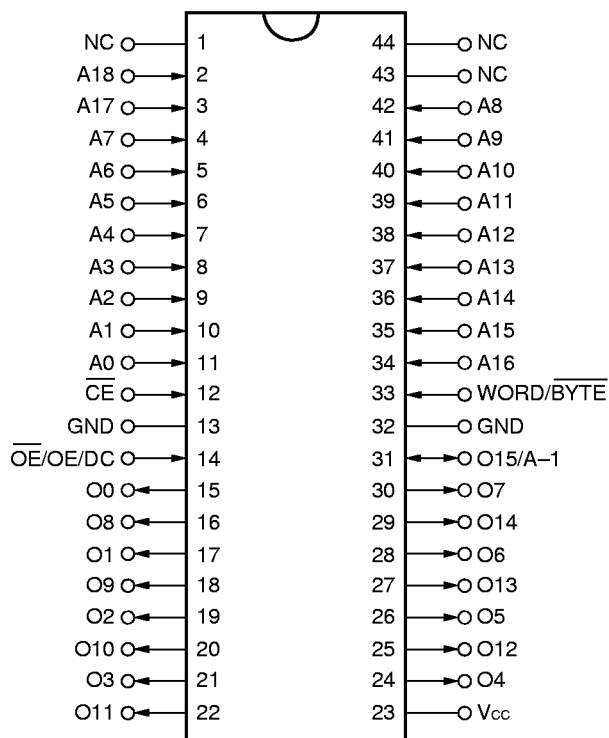
42-pin Plastic DIP (600 mil)

[μPD23C8000XCZ]



44-pin Plastic SOP (600 mil)

[μPD23C8000XGX]

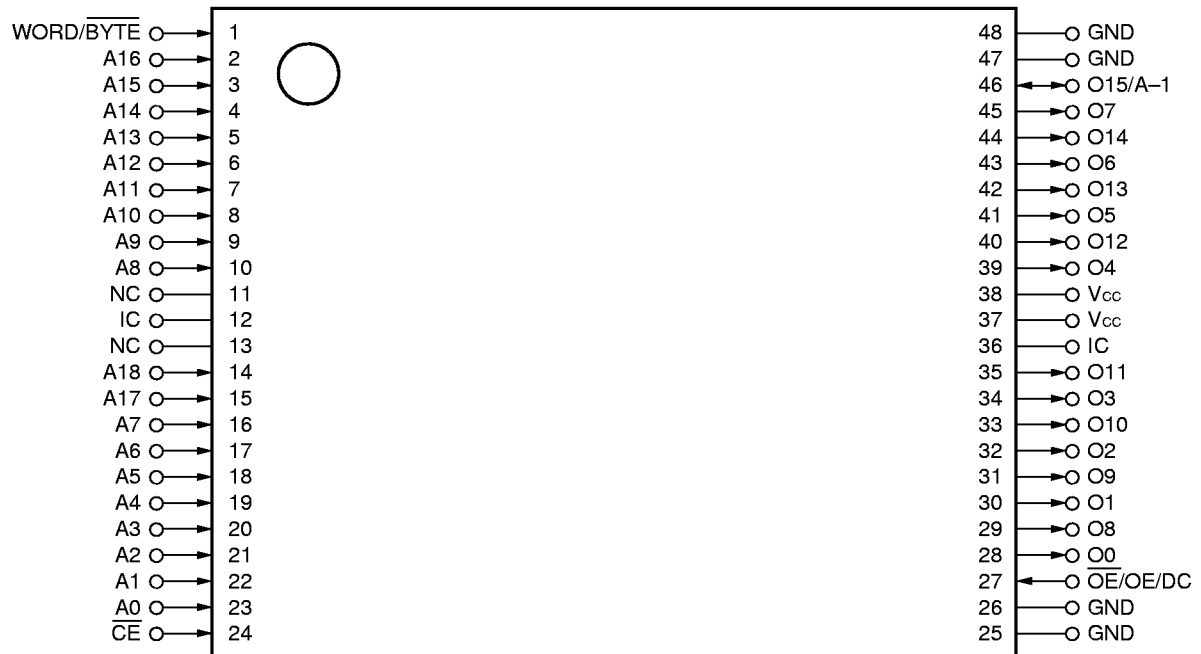


- A0-A18 : Address inputs
 O0-O7, O8-O14 : Data outputs
 O15/A-1 : Data 15 output (WORD mode) /LSB address input (BYTE mode)
 WORD/BYTE : Mode select
 CE : Chip enable
 OE/OE : Output enable
 Vcc : Supply voltage
 GND : Ground
 NC^{Note 1} : No connection
 IC^{Note 2} : Internal connection
 DC : Don't care

- Notes** 1. Some signals can be applied because this pin is not connected to the inside of the chip.
 2. Leave this pin unconnected or connect to GND.

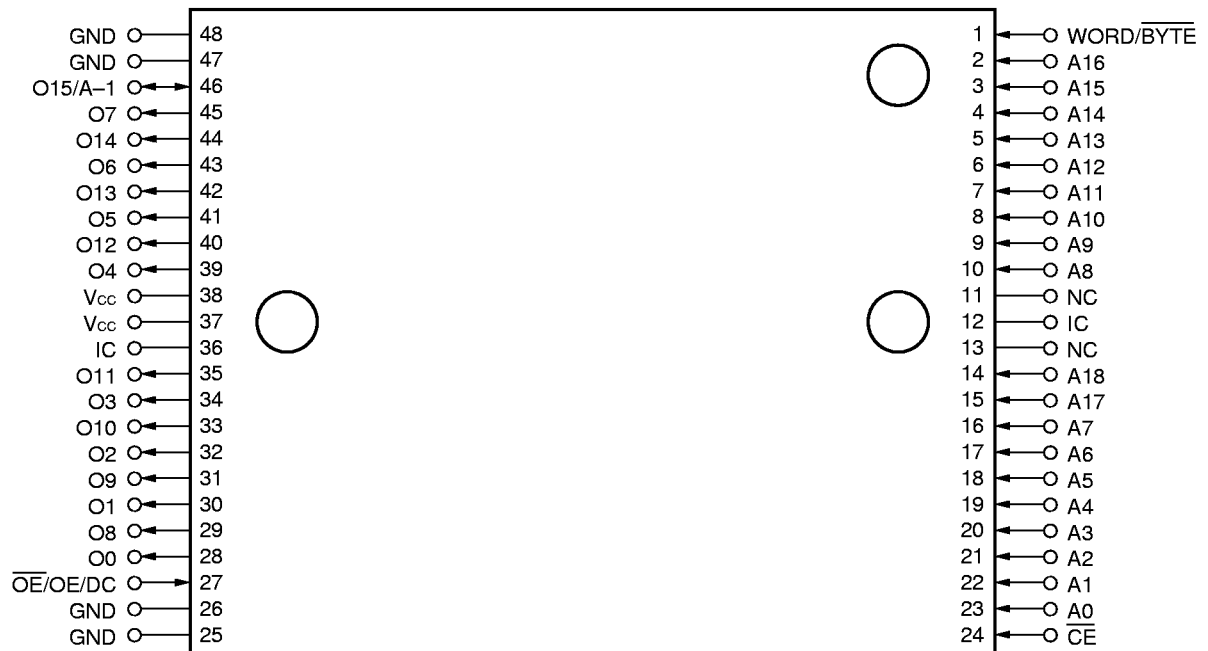
48-pin Plastic TSOP (I) (12 × 18mm) (Normal bent)

[μPD23C8000XGY-MJH]

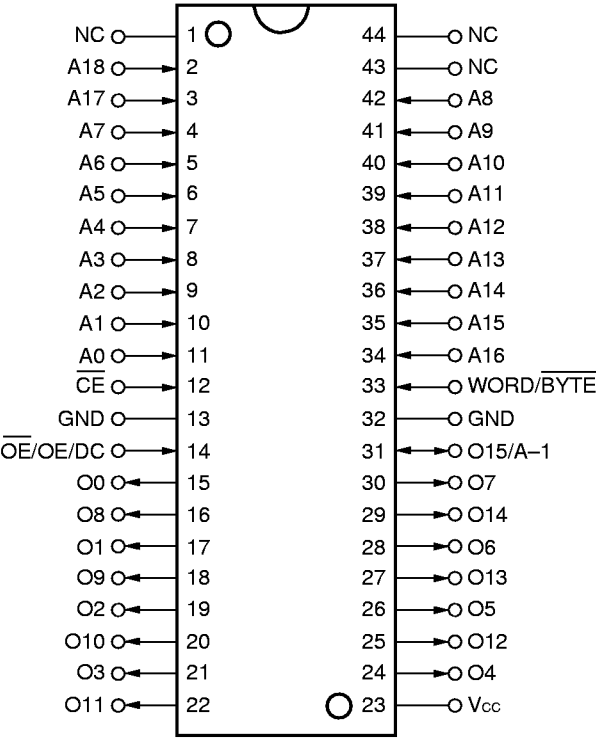


48-pin Plastic TSOP (I) 12 × 18mm) (Reverse bent)

[μPD23C8000XGY-MKH]



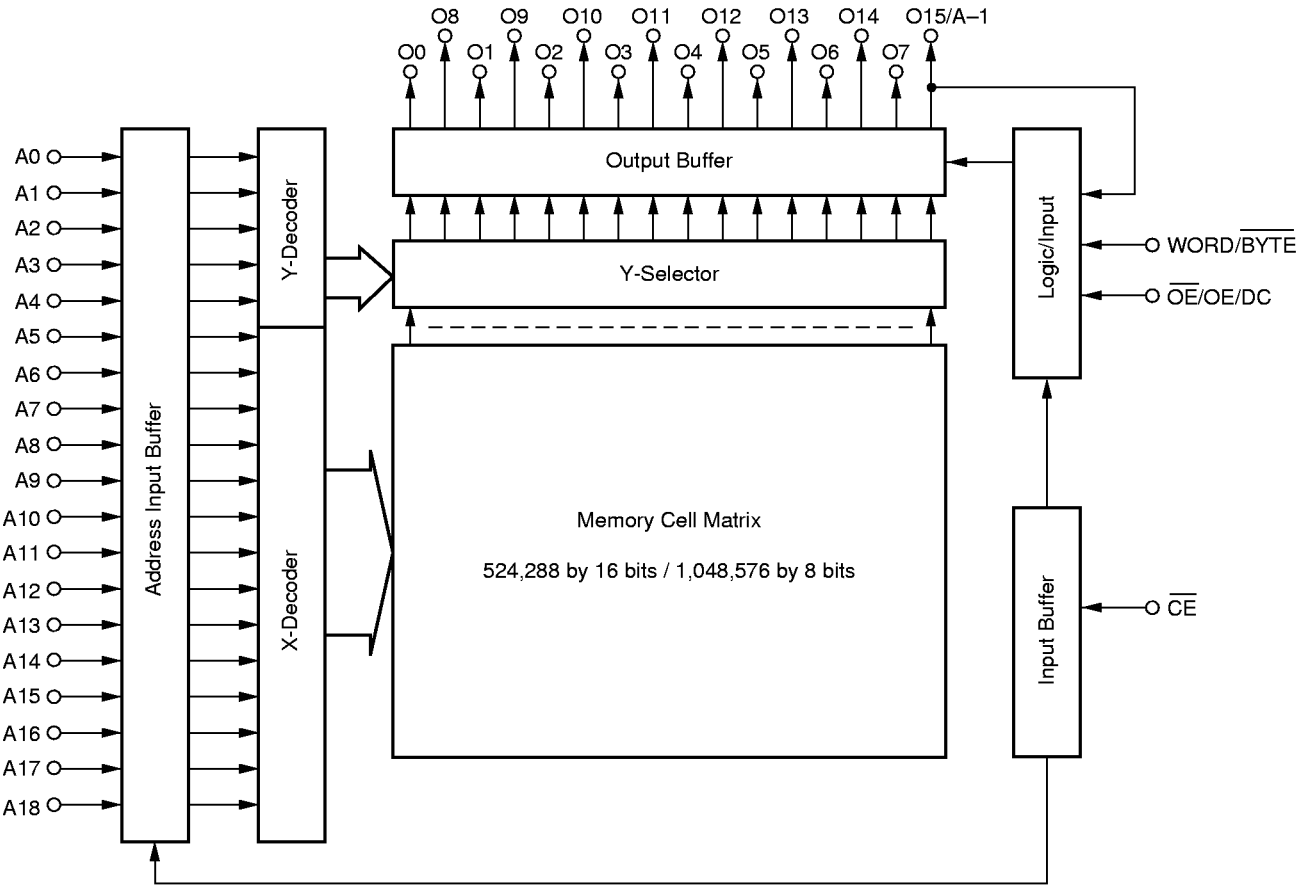
44-pin Plastic TSOP (II) (400 mil) (Normal bent)
[μPD23C8000XG5-7JF]



Input/Output Pin Functions

Pin name	Input/ Output	Function
WORD/BYTE	Input	The pin for switching word mode and byte mode. High level Word mode (512K-word by 16 bits) Low level Byte mode (1M-word by 8 bits)
A0 to A18 (Address input)		Address bus. A0 to A18 are used differently in the word mode (512K-word by 16 bits) and the byte mode (1M-word by 8 bits). Word mode A0 to A18 are used as 19 bits address signals. Byte mode A0 to A18 are used as the upper 19 bits of total 20 bits of address signal. (The least significant bit (A-1) is combined to O15.)
O0 to O7, O8 to O14 (Data output)	Output	Output data bus. O0 to O7, O8 to O14 are used differently in the word (512K-word by 16 bits) and the byte mode (1M-word by 8 bits). Word mode The lower 15 bits of 16 bits data outputs to O0 to O14. (The most significant bit (O15) combined to A-1.) Byte mode 8 bits data outputs to O0 to O7 and also O8 to O14 is high impedance.
O15/A-1 (Data output 15)/ (LSB Address input)	Output / Input	O15/A-1 are used differently in the word (512K-word by 16 bits) and the byte mode (1M-word by 8 bits). Word mode The most significant output data bus (O15). Byte mode The least significant address bus (A-1).
$\overline{CE}$ (Chip Enable)	Input	Chip activating signal. When the OE is active, output states are followings. High level High impedance Low level Data out
$\overline{OE}/OE/DC$ (Output Enable / Don't care)		Output enable signal. The active level of OE is mask option. The active level of OE can be selected from high active, low active and Don't care at order.
Vcc	—	Supply voltage
GND	—	Ground
NC	—	Not internally connected. (The signal can be connected.)
IC	—	Internally connected. (Leave this pin unconnected or connect to GND.)

Block Diagram



Mask Option

The active levels of output enable pin ($\overline{\text{OE}}$ /OE/DC) are mask programmable and optional, and can be selected from among "0" "1" "X" shown in the table below.

Option	$\overline{\text{OE}}$ /OE/DC	OE active level
0	$\overline{\text{OE}}$	L
1	OE	H
X	DC	Don't care

Operation modes for each option are shown in the tables below.

Operation mode (Option : 0)

$\overline{\text{CE}}$	$\overline{\text{OE}}$	Mode	Output state
L	L	Active	Data out
	H		High impedance
H	H or L	Standby	High impedance

Operation mode (Option : 1)

$\overline{\text{CE}}$	OE	Mode	Output state
L	L	Active	High impedance
	H		Data out
H	H or L	Standby	High impedance

Operation mode (Option : X)

$\overline{\text{CE}}$	DC	Mode	Output state
L	H or L	Active	Data out
H	H or L	Standby	High impedance

Remark L : Low level input

H : High level input

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V_{CC}		-0.3 to +7.0	V
Input voltage	V_I		-0.3 to $V_{CC} + 0.3$	V
Output voltage	V_O		-0.3 to $V_{CC} + 0.3$	V
Operating ambient temperature	T_A		-10 to +70	°C
Storage temperature	T_{stg}		-65 to +150	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational sections of this specification. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Capacitance ($T_A = 25\text{ °C}$)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C_i	$f = 1\text{ MHz}$			10	pF
Output capacitance	C_o				12	pF

DC Characteristics ($T_A = -10\text{ to }+70\text{ °C}$, $V_{CC} = 5\text{ V} \pm 10\%$)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
High level input voltage	V_{IH}		2.2		$V_{CC} + 0.3$	V
Low level input voltage	V_{IL}		-0.3		+0.8	V
High level output voltage	V_{OH1}	$I_{OH} = -400\text{ }\mu\text{A}$	2.4			V
	V_{OH2}	$I_{OH} = -100\text{ }\mu\text{A}$	$V_{CC} - 0.5$			
Low level output voltage	V_{OL}	$I_{OL} = 2.1\text{ mA}$			0.4	V
Input leakage current	I_{LI}	$V_I = 0\text{ to }V_{CC}$	-10		+10	μA
Output leakage current	I_{LO}	$V_O = 0\text{ to }V_{CC}$, Chip deselected	-10		+10	μA
Power supply current	I_{CC1}	$\overline{CE} = V_{IL}$ (Active mode), $I_O = 0\text{ mA}$			50	mA
Standby current	I_{CC2}	$\overline{CE} = V_{IH}$ (Standby mode)			1.5	mA
	I_{CC3}	$\overline{CE} = V_{CC} - 0.2\text{ V}$ (Standby mode)			100	μA

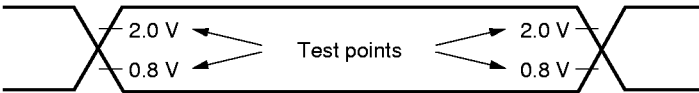
AC Characteristics (TA = -10 to +70 °C, Vcc = 5 V ±10%)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Address access time	tACC				120	ns
Chip enable access time	tCE				120	ns
Output enable access time	tOE				50	ns
Output hold time	tOH		0			ns
Output disable time	tDF		0		25	ns
WORD/BYTE access time	tWB				120	ns

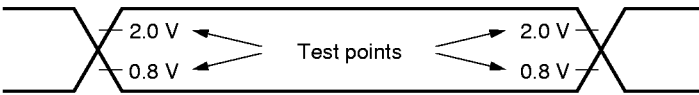
Remark tDF is the time from inactivation of $\overline{CE}$ or $\overline{OE}/OE$ to high-impedance state output.

AC Test Conditions

Input waveform (Rise/Fall time ≤ 5 ns)



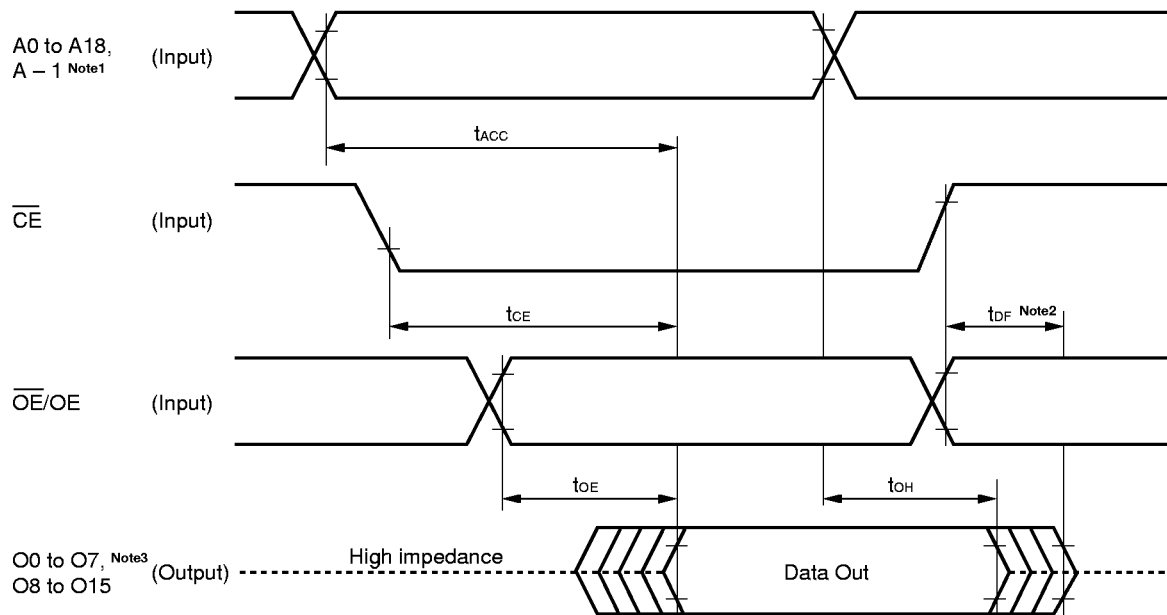
Output waveform



Output load

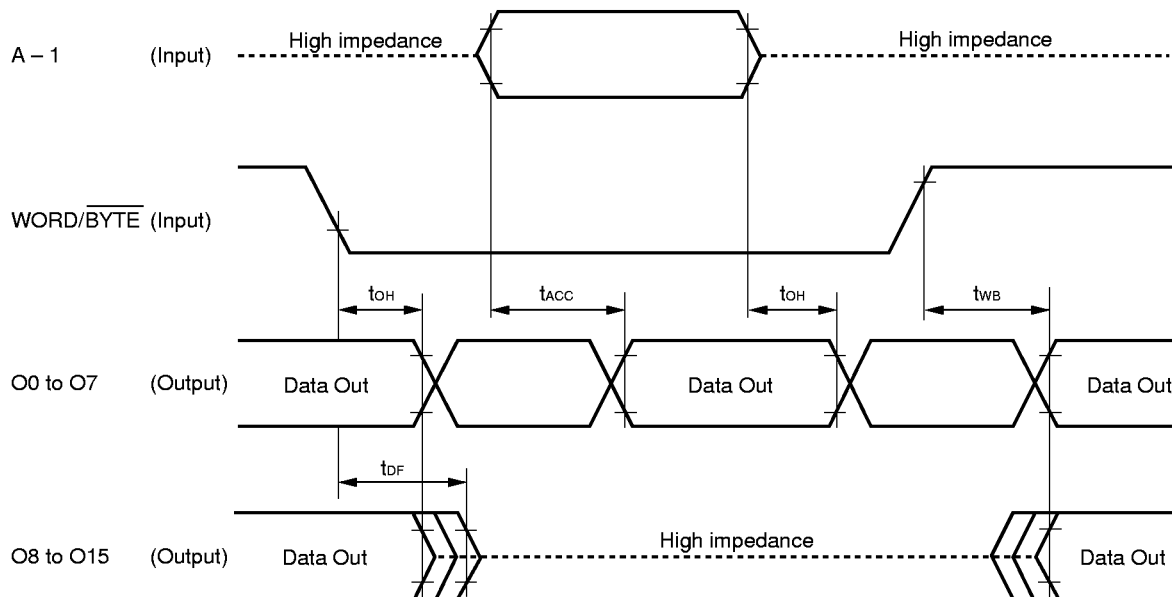
1TTL+100pF

Read Cycle Timing Chart



- Notes**
1. During WORD mode, A-1 is O15.
 2. t_{DF} is specified when the one of $\overline{CE}$, $\overline{OE}/OE$ is inactivated.
 3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.

WORD Mode, BYTE Mode Switch Timing Chart



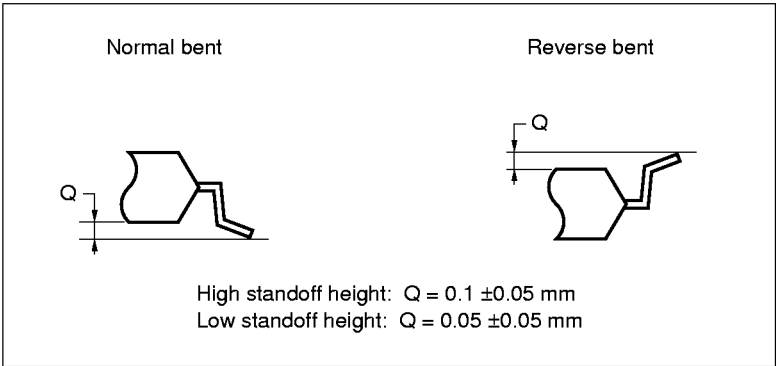
Remark $\overline{OE}/OE$, $\overline{CE}$: Active.

★ Notice of change in 48-pin TSOP (I) standoff height

We are changing the 48-pin TSOP (I) standoff height 0.05 ± 0.05 mm (low standoff height) to 0.1 ± 0.05 mm (high standoff height). Each lot version is identified by the fifth character of the lot number.

Difference between high standoff height and low standoff height

Detail of lead end

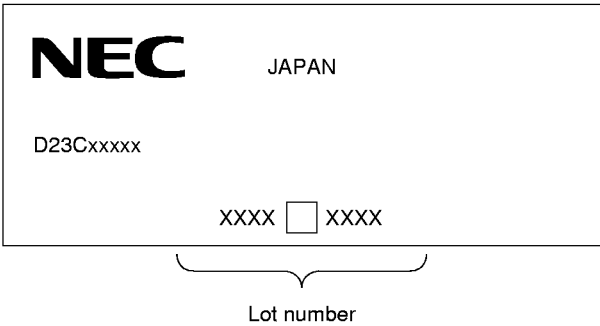


Identification of each lot version

Each lot version is identified by the fifth character of the lot number.

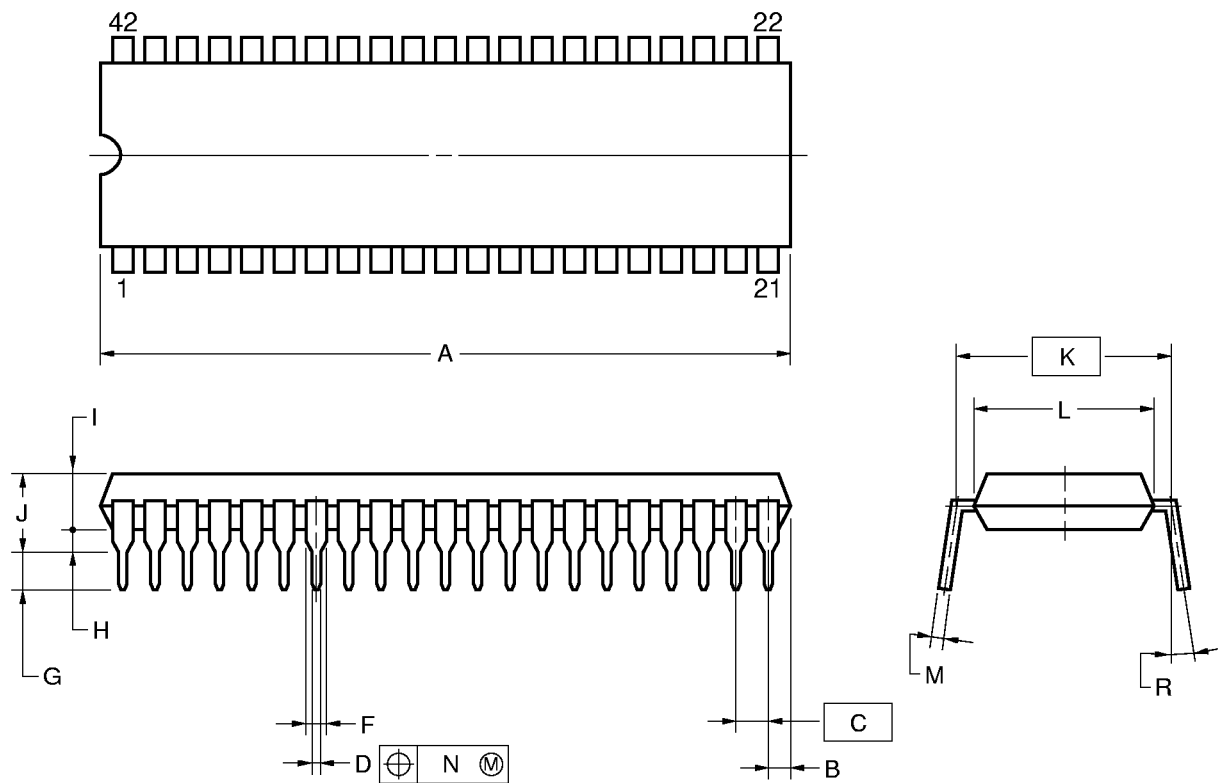
Fifth character of the lot number	Lot version	Standoff height
L	L version	0.1 ± 0.05 mm (High standoff height)
K	K version	0.05 ± 0.05 mm (Low standoff height)

Marking Example



★ Package Drawings

42PIN PLASTIC DIP (600 mil)



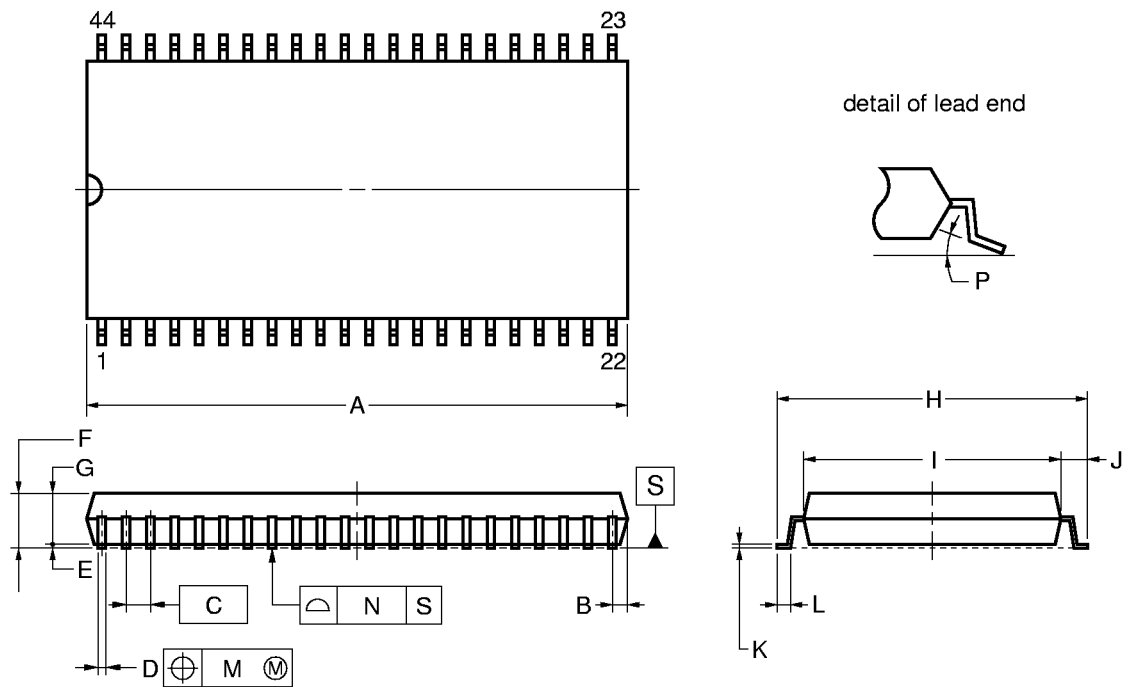
NOTES

- 1) Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

ITEM	MILLIMETERS	INCHES
A	55.88 MAX.	2.200 MAX.
B	2.54 MAX.	0.100 MAX.
C	2.54 (T.P.)	0.100 (T.P.)
D	0.50±0.10	0.020 ^{+0.004} _{-0.005}
F	1.2 MIN.	0.047 MIN.
G	3.6±0.3	0.142±0.012
H	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.72 MAX.	0.226 MAX.
K	15.24 (T.P.)	0.600 (T.P.)
L	13.2	0.520
M	0.25 ^{+0.10} _{-0.05}	0.010 ^{+0.004} _{-0.003}
N	0.25	0.01
R	0~15°	0~15°

P42C-100-600A,B-1

44 PIN PLASTIC SOP (600 mil)



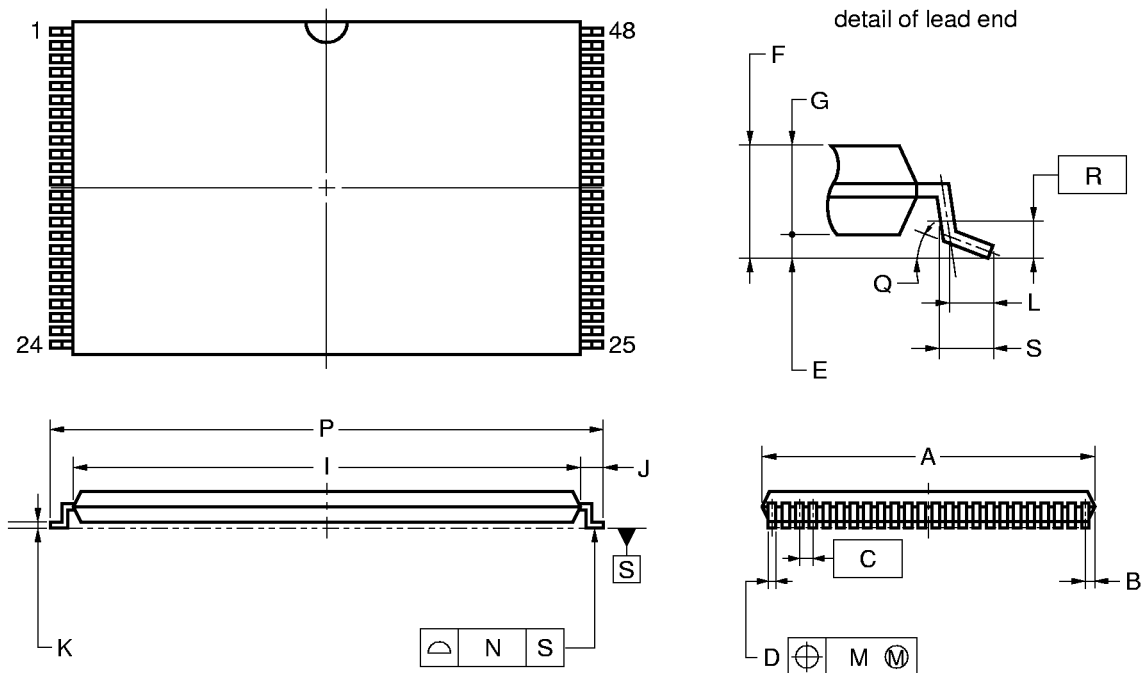
- NOTE**
- 1. Controlling dimension — millimeter.
 - 2. Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	27.83 ^{+0.4} _{-0.05}	1.096 ^{+0.016} _{-0.003}
B	0.78 MAX.	0.031 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.42 ^{+0.08} _{-0.07}	0.017 ^{+0.003} _{-0.004}
E	0.15±0.1	0.006±0.004
F	3.0 MAX.	0.119 MAX.
G	2.7±0.05	0.106 ^{+0.003} _{-0.002}
H	16.04±0.3	0.631 ^{+0.013} _{-0.012}
I	13.24±0.1	0.521 ^{+0.005} _{-0.004}
J	1.4±0.2	0.055±0.008
K	0.22 ^{+0.08} _{-0.07}	0.009 ^{+0.003} _{-0.004}
L	0.8±0.2	0.031 ^{+0.009} _{-0.008}
M	0.12	0.005
N	0.10	0.004
P	3° ^{+7°} _{-3°}	3° ^{+7°} _{-3°}

P44GX-50-600A-3

L Version: High standoff height

48 PIN PLASTIC TSOP (I) (12×18)



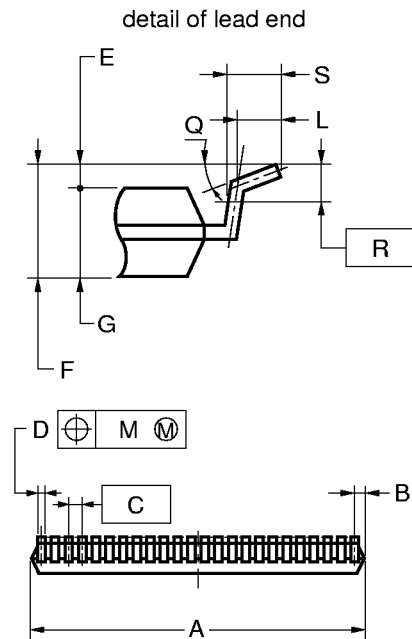
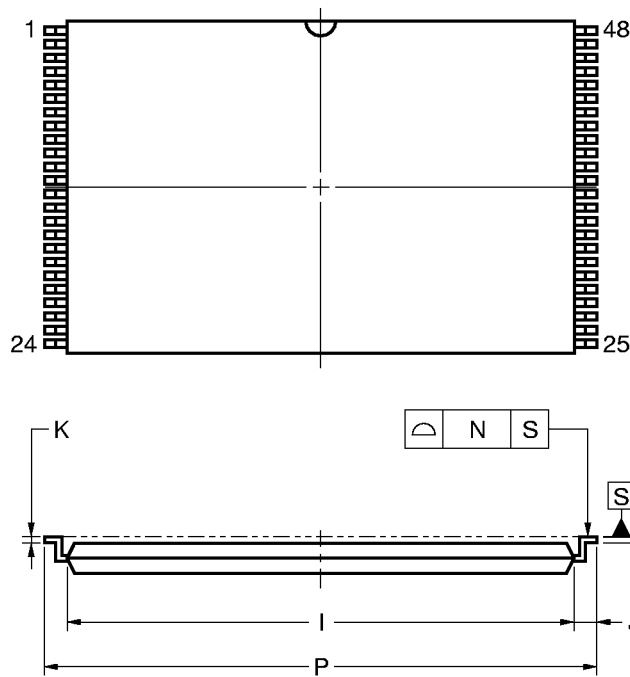
- NOTES**
- 1. Controlling dimension — Millimeter.
 - 2. Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.
 - 3. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX. <0.489 inch MAX.>)

ITEM	MILLIMETERS	INCHES
A	12.0±0.1	0.472 ^{+0.005} _{-0.004}
B	0.45 MAX.	0.018 MAX.
C	0.5 (T.P.)	0.020 (T.P.)
D	0.22±0.05	0.009 ^{+0.002} _{-0.003}
E	0.1±0.05	0.004±0.002
F	1.2 MAX.	0.048 MAX.
G	1.0±0.05	0.039 ^{+0.003} _{-0.002}
I	16.4±0.1	0.646 ^{+0.004} _{-0.005}
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.145±0.05	0.006 ^{+0.002} _{-0.003}
L	0.5	0.020
M	0.10	0.004
N	0.10	0.004
P	18.0±0.2	0.709 ^{+0.008} _{-0.009}
Q	3° ^{+5°} _{-3°}	3° ^{+5°} _{-3°}
R	0.25	0.010
S	0.60±0.15	0.024 ^{+0.006} _{-0.007}

S48GY-50-MJH1

L Version: High standoff height

48 PIN PLASTIC TSOP (I) (12×18)



NOTES

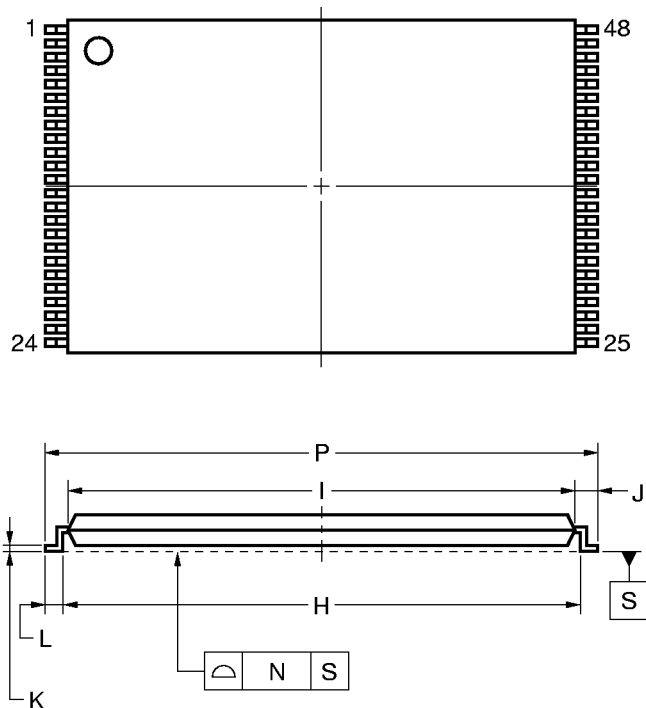
1. Controlling dimension — Millimeter.
2. Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.
3. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX. <0.489 inch MAX.>)

ITEM	MILLIMETERS	INCHES
A	12.0±0.1	0.472 ^{+0.005} _{-0.004}
B	0.45 MAX.	0.018 MAX.
C	0.5 (T.P.)	0.020 (T.P.)
D	0.22±0.05	0.009 ^{+0.002} _{-0.003}
E	0.1±0.05	0.004±0.002
F	1.2 MAX.	0.048 MAX.
G	1.0±0.05	0.039 ^{+0.003} _{-0.002}
I	16.4±0.1	0.646 ^{+0.004} _{-0.005}
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.145±0.05	0.006 ^{+0.002} _{-0.003}
L	0.5	0.020
M	0.10	0.004
N	0.10	0.004
P	18.0±0.2	0.709 ^{+0.008} _{-0.009}
Q	3° ^{+5°} _{-3°}	3° ^{+5°} _{-3°}
R	0.25	0.010
S	0.60±0.15	0.024 ^{+0.006} _{-0.007}

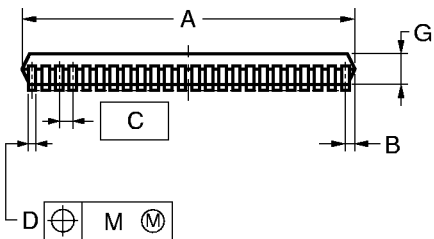
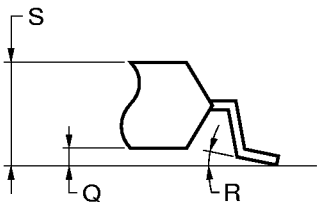
S48GY-50-MKH1

K Version: Low standoff height

48 PIN PLASTIC TSOP (I) (12x18)



detail of lead end



NOTES

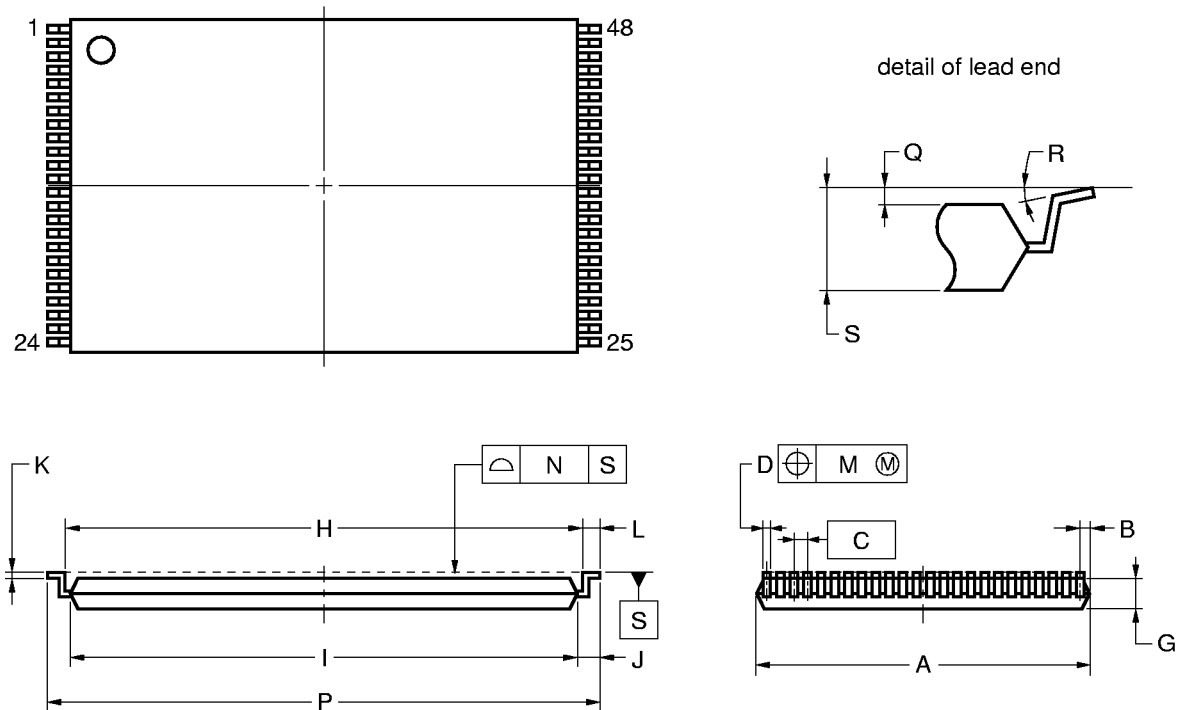
1. Controlling dimension — millimeter.
2. Each lead centerline is located within 0.08 mm (0.003 inch) of its true position (T.P.) at maximum material condition.
3. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX. <0.489 inch MAX.>)

ITEM	MILLIMETERS	INCHES
A	12.0±0.1	0.472 ^{+0.005} _{-0.004}
B	0.45 MAX.	0.018 MAX.
C	0.5 (T.P.)	0.020 (T.P.)
D	0.22 ^{+0.08} _{-0.07}	0.009 ^{+0.003} _{-0.004}
G	0.97	0.038
H	17.0±0.2	0.669 ^{+0.009} _{-0.008}
I	16.4±0.1	0.646 ^{+0.004} _{-0.005}
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.145 ^{+0.03} _{-0.055}	0.006 ^{+0.001} _{-0.003}
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.08	0.003
N	0.10	0.004
P	18.0±0.2	0.709 ^{+0.008} _{-0.009}
Q	0.05±0.05	0.002±0.002
R	2°+4° -2°	2°+4° -2°
S	1.02±0.08	0.040 ^{+0.004} _{-0.003}

S48GY-50-MJH-3

K Version: Low standoff height

48 PIN PLASTIC TSOP (I) (12x18)



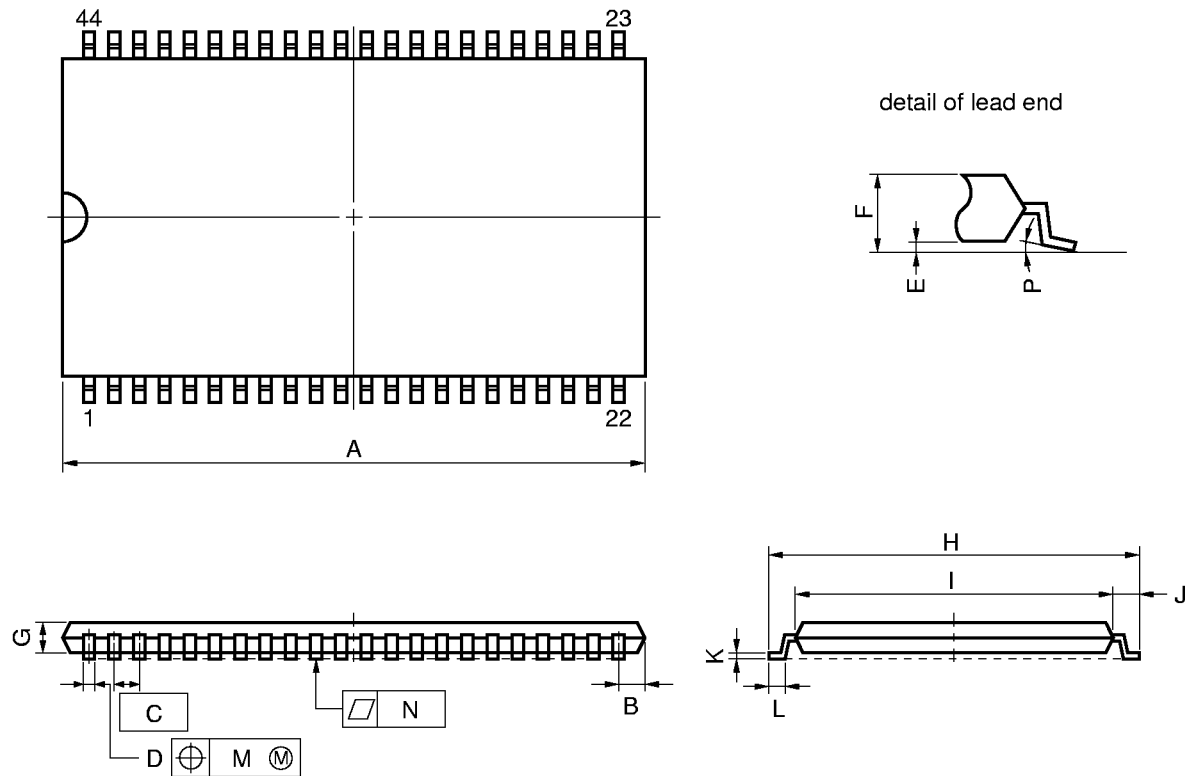
NOTES

- 1. Controlling dimension — millimeter.
- 2. Each lead centerline is located within 0.08 mm (0.003 inch) of its true position (T.P.) at maximum material condition.
- 3. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX. <0.489 inch MAX.>)

ITEM	MILLIMETERS	INCHES
A	12.0±0.1	0.472 ^{+0.005} _{-0.004}
B	0.45 MAX.	0.018 MAX.
C	0.5 (T.P.)	0.020 (T.P.)
D	0.22 ^{+0.08} _{-0.07}	0.009 ^{+0.003} _{-0.004}
G	0.97	0.038
H	17.0±0.2	0.669 ^{+0.009} _{-0.008}
I	16.4±0.1	0.646 ^{+0.004} _{-0.005}
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.145 ^{+0.03} _{-0.055}	0.006 ^{+0.001} _{-0.003}
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.08	0.003
N	0.10	0.004
P	18.0±0.2	0.709 ^{+0.008} _{-0.009}
Q	0.05±0.05	0.002±0.002
R	2° ^{+4°} _{-2°}	2° ^{+4°} _{-2°}
S	1.02±0.08	0.040 ^{+0.004} _{-0.003}

S48GY-50-MKH-3

44 PIN PLASTIC TSOP(II) (400 mil)



NOTE
Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	18.63 MAX.	0.734 MAX.
B	0.93 MAX.	0.037 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.32 ^{+0.08} _{-0.07}	0.013±0.003
E	0.1±0.05	0.004±0.002
F	1.2 MAX.	0.048 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.145 ^{+0.025} _{-0.015}	0.006±0.001
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.13	0.005
N	0.10	0.004
P	3° ^{+7°} _{-3°}	3° ^{+7°} _{-3°}

S44G5-80-7JF5

Recommended Soldering Conditions

The following conditions (see table below) must be met when soldering the μPD23C8000X.

For more details, refer to our document “**SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL**” (C10535E).

Please consult with our sales offices in case other soldering process is used, or in case soldering is done under different conditions.

Types of Surface Mount Device

μPD23C8000XGX : 44-pin Plastic SOP (600 mil)

μPD23C8000XGY-MJH : 48-pin Plastic TSOP (I) (12 × 18 mm) (Normal bent)

μPD23C8000XGY-MKH : 48-pin Plastic TSOP (I) (12 × 18 mm) (Reverse bent)

μPD23C8000XG5-7JF : 44-pin Plastic TSOP (II) (400 mil) (Normal bent)

Please consult with our sales offices.

Type of Through Hole Mount Device

μPD23C8000XCZ : 42-pin Plastic DIP (600 mil)

Soldering process	Soldering conditions
Wave soldering (Only to leads)	Solder temperature: 260 °C or below, Flow time: 10 seconds or below
Partial heating method	Terminal temperature: 300 °C or below, Time: 3 seconds or below (Per one lead)

Caution Do not jet molten solder on the surface of package.